



**General Description**

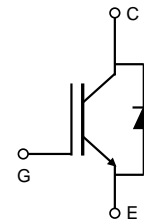
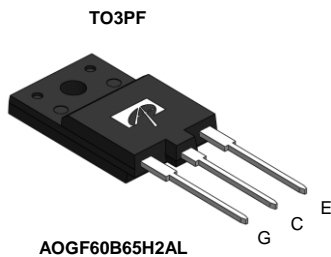
- Latest AlphaGBT (αIGBT) Technology
- 650V breakdown voltage
- Very fast and soft recovery freewheeling diode
- High efficient turn-on di/dt controllability
- Very high switching speed
- Low turn-off switching loss and softness
- Very good EMI behavior

**Applications**

- Power factor correction
- Very high switching frequency applications

**Product Summary**

$V_{CE}$	650V
$I_C$ ( $T_C=100^\circ\text{C}$ )	60A
$V_{CE(sat)}$ ( $T_J=25^\circ\text{C}$ )	1.95V



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOGF60B65H2AL	TO3PF	Tube	480

**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	AOGF60B65H2AL	Units
Collector-Emitter Voltage	$V_{CE}$	650	V
Gate-Emitter Voltage	$V_{GE}$	$\pm 30$	V
Continuous Collector Current	$I_C$	$T_C=25^\circ\text{C}$	120 <sup>(1)</sup>
		$T_C=100^\circ\text{C}$	60 <sup>(1)</sup>
Pulsed Collector Current, Limited by $T_{Jmax}$	$I_{CM}$	180	A
Turn-Off SOA, $V_{CE} \leq 650\text{V}$ , Limited by $T_{Jmax}$	$I_{LM}$	180	A
Continuous Diode Forward Current	$I_F$	$T_C=25^\circ\text{C}$	60 <sup>(1)</sup>
		$T_C=100^\circ\text{C}$	30 <sup>(1)</sup>
Diode Pulsed Current, Limited by $T_{Jmax}$	$I_{FM}$	90	A
Power Dissipation	$P_D$	$T_C=25^\circ\text{C}$	74
		$T_C=100^\circ\text{C}$	29
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purpose, 1/8" from case for 5 seconds	$T_L$	300	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	AOGF60B65H2AL	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	30	$^\circ\text{C/W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	1.7	$^\circ\text{C/W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	2.5	$^\circ\text{C/W}$

(1) TO3PF  $I_C, I_F$  follows TO247.

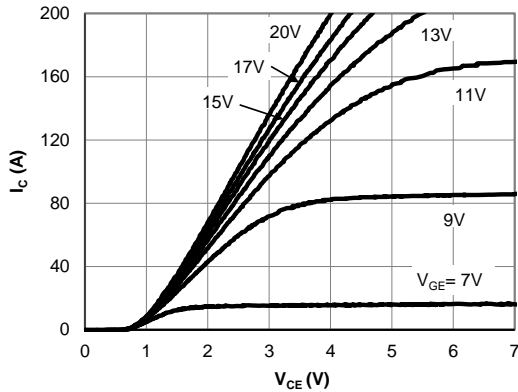
**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
<b>STATIC PARAMETERS</b>							
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =1mA, V <sub>GE</sub> =0V, T <sub>J</sub> =25°C	650	-	-	V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	V <sub>GE</sub> =15V, I <sub>C</sub> =60A	T <sub>J</sub> =25°C	-	1.95	2.5	V
			T <sub>J</sub> =125°C	-	2.45	-	
			T <sub>J</sub> =150°C	-	2.58	-	
V <sub>F</sub>	Diode Forward Voltage	V <sub>GE</sub> =0V, I <sub>F</sub> =30A	T <sub>J</sub> =25°C	-	1.88	2.4	V
			T <sub>J</sub> =125°C	-	1.97	-	
			T <sub>J</sub> =150°C	-	1.94	-	
V <sub>GE(th)</sub>	Gate-Emitter Threshold Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	-	4.6	-	V	
I <sub>CES</sub>	Zero Gate Voltage Collector Current	V <sub>CE</sub> =650V, V <sub>GE</sub> =0V	T <sub>J</sub> =25°C	-	-	10	μA
			T <sub>J</sub> =125°C	-	-	1000	
			T <sub>J</sub> =150°C	-	-	5000	
I <sub>GES</sub>	Gate-Emitter Leakage Current	V <sub>CE</sub> =0V, V <sub>GE</sub> =±30V	-	-	±100	nA	
g <sub>FS</sub>	Forward Transconductance	V <sub>CE</sub> =20V, I <sub>C</sub> =60A	-	33	-	S	
<b>DYNAMIC PARAMETERS</b>							
C <sub>ies</sub>	Input Capacitance	V <sub>GE</sub> =0V, V <sub>CC</sub> =25V, f=1MHz	-	2100	-	pF	
C <sub>oes</sub>	Output Capacitance		-	185	-	pF	
C <sub>res</sub>	Reverse Transfer Capacitance		-	65	-	pF	
Q <sub>g</sub>	Total Gate Charge	V <sub>GE</sub> =15V, V <sub>CC</sub> =520V, I <sub>C</sub> =60A	-	84	-	nC	
Q <sub>ge</sub>	Gate to Emitter Charge		-	21	-	nC	
Q <sub>gc</sub>	Gate to Collector Charge		-	38	-	nC	
R <sub>g</sub>	Gate Resistance	V <sub>GE</sub> =0V, V <sub>CC</sub> =0V, f=1MHz	-	15	-	Ω	
<b>SWITCHING PARAMETERS, (Load Inductive, T<sub>J</sub>=25°C)</b>							
t <sub>D(on)</sub>	Turn-On Delay Time	T <sub>J</sub> =25°C V <sub>GE</sub> =15V, V <sub>CC</sub> =400V, I <sub>C</sub> =60A, R <sub>G</sub> =5Ω	-	35	-	ns	
t <sub>r</sub>	Turn-On Rise Time		-	80	-	ns	
t <sub>D(off)</sub>	Turn-Off Delay Time		-	168	-	ns	
t <sub>f</sub>	Turn-Off Fall Time		-	76	-	ns	
E <sub>on</sub>	Turn-On Energy		-	2.36	-	mJ	
E <sub>off</sub>	Turn-Off Energy		-	1.17	-	mJ	
E <sub>total</sub>	Total Switching Energy		-	3.54	-	mJ	
t <sub>rr</sub>	Diode Reverse Recovery Time		T <sub>J</sub> =25°C	-	318	-	ns
Q <sub>rr</sub>	Diode Reverse Recovery Charge		I <sub>F</sub> =30A, di/dt=200A/μs, V <sub>CC</sub> =400V	-	0.8	-	μC
I <sub>rm</sub>	Diode Peak Reverse Recovery Current		-	6.0	-	A	
<b>SWITCHING PARAMETERS, (Load Inductive, T<sub>J</sub>=150°C)</b>							
t <sub>D(on)</sub>	Turn-On Delay Time	T <sub>J</sub> =150°C V <sub>GE</sub> =15V, V <sub>CC</sub> =400V, I <sub>C</sub> =60A, R <sub>G</sub> =5Ω	-	33	-	ns	
t <sub>r</sub>	Turn-On Rise Time		-	80	-	ns	
t <sub>D(off)</sub>	Turn-Off Delay Time		-	195	-	ns	
t <sub>f</sub>	Turn-Off Fall Time		-	75	-	ns	
E <sub>on</sub>	Turn-On Energy		-	2.53	-	mJ	
E <sub>off</sub>	Turn-Off Energy		-	1.51	-	mJ	
E <sub>total</sub>	Total Switching Energy		-	4.04	-	mJ	
t <sub>rr</sub>	Diode Reverse Recovery Time		T <sub>J</sub> =150°C	-	427	-	ns
Q <sub>rr</sub>	Diode Reverse Recovery Charge		I <sub>F</sub> =30A, di/dt=200A/μs, V <sub>CC</sub> =400V	-	1.6	-	μC
I <sub>rm</sub>	Diode Peak Reverse Recovery Current		-	7.5	-	A	

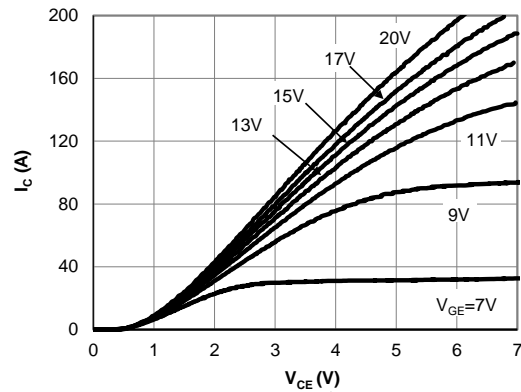
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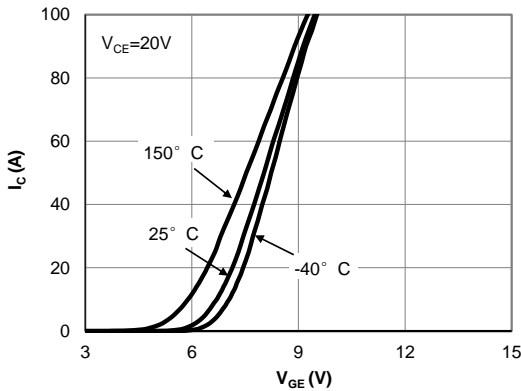
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



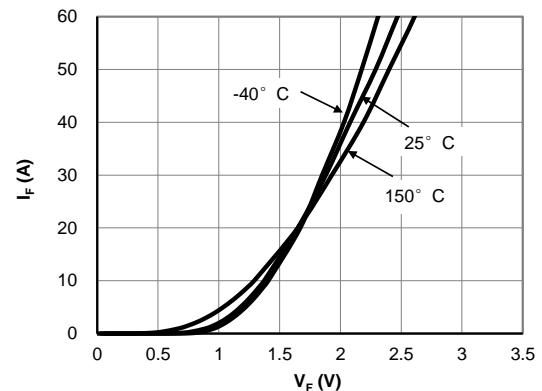
**Figure 1: Output Characteristic**  
( $T_j=25^\circ\text{C}$ )



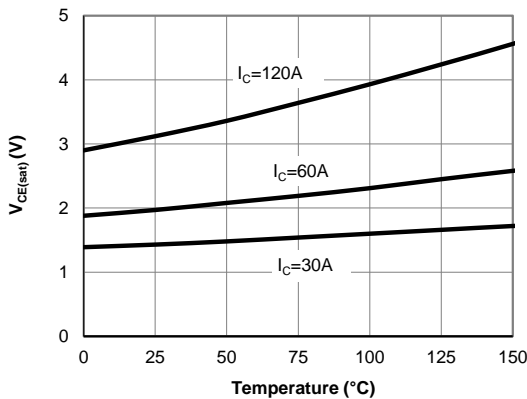
**Figure 2: Output Characteristic**  
( $T_j=150^\circ\text{C}$ )



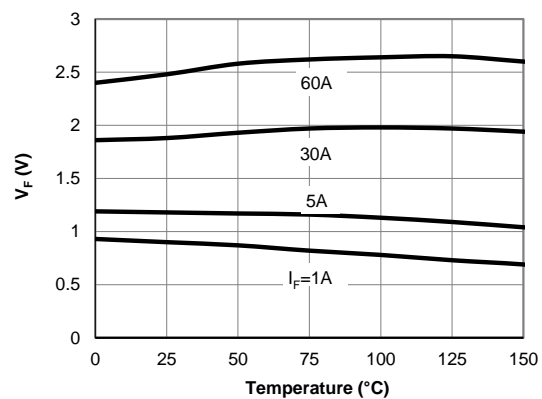
**Figure 3: Transfer Characteristic**



**Figure 4: Diode Characteristic**



**Figure 5: Collector-Emitter Saturation Voltage vs. Junction Temperature**



**Figure 6: Diode Forward voltage vs. Junction Temperature**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

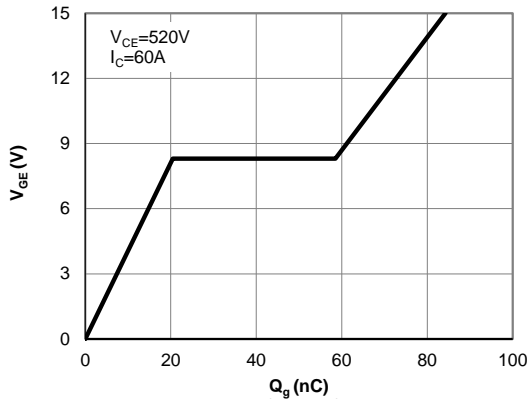


Figure 7: Gate-Charge Characteristics

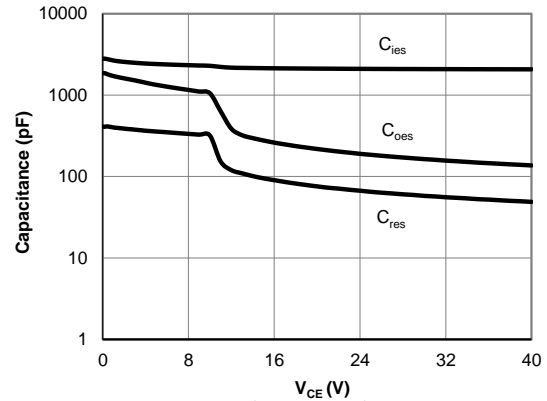


Figure 8: Capacitance Characteristic

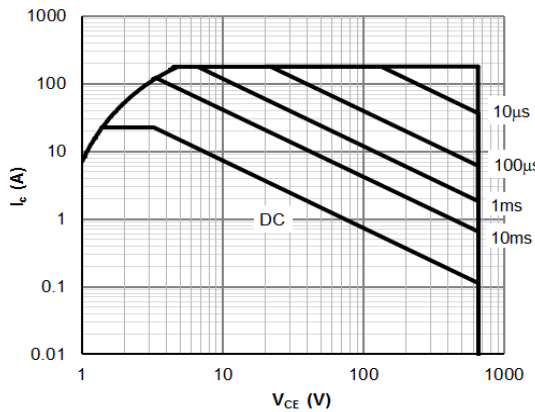


Figure 9: Forward Bias Safe Operating Area  
( $T_C=25^{\circ}\text{C}$ ,  $V_{GE}=15\text{V}$ )

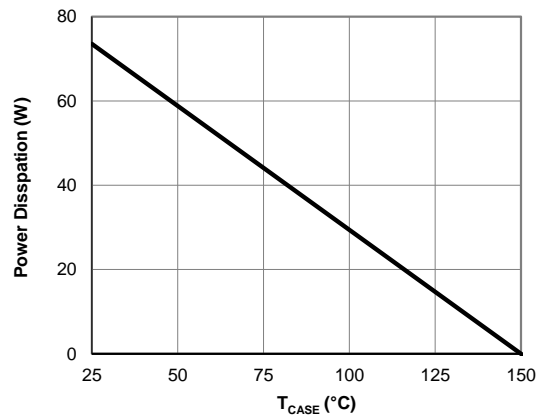


Figure 10: Power Dissipation as a Function of Case

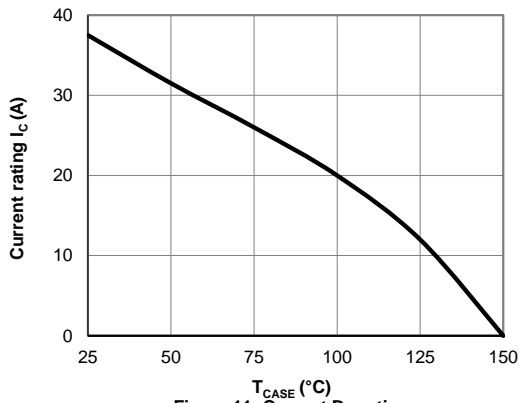


Figure 11: Current De-rating

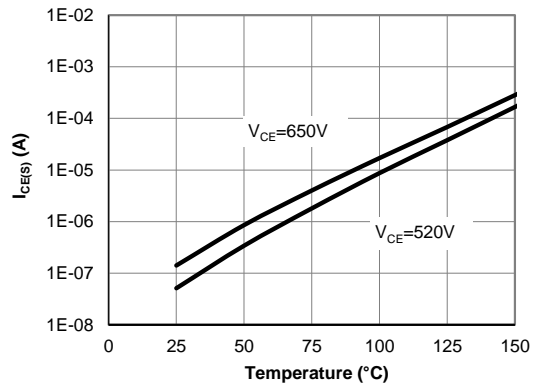
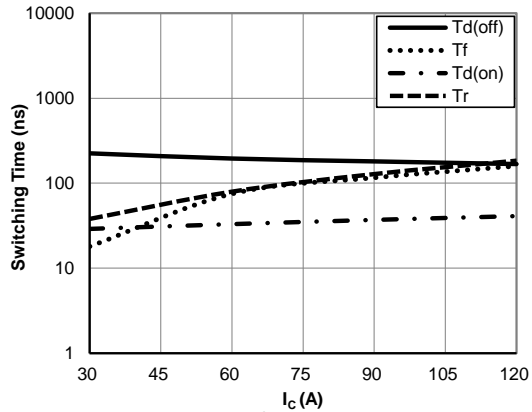
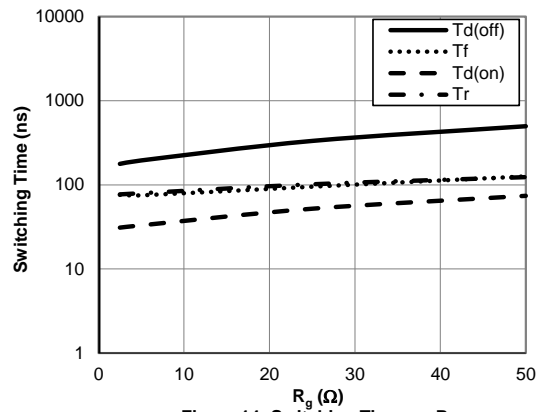


Figure 12: Diode Reverse Leakage Current vs. Junction Temperature

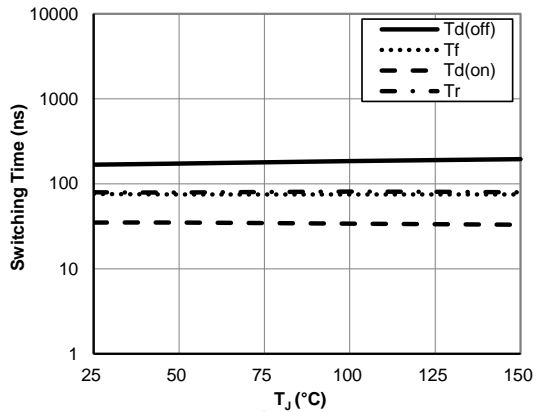
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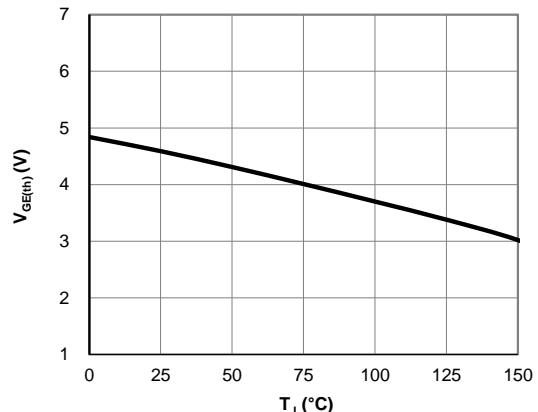
**Figure 13: Switching Time vs.  $I_C$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $R_g=5\Omega$ )



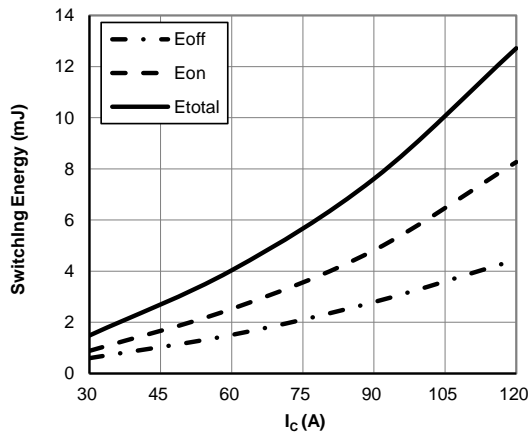
**Figure 14: Switching Time vs.  $R_g$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $I_C=60\text{A}$ )



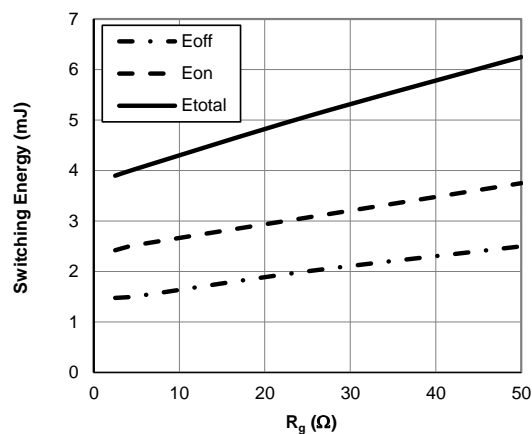
**Figure 15: Switching Time vs.  $T_J$**   
( $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $I_C=60\text{A}$ ,  $R_g=5\Omega$ )



**Figure 16:  $V_{GE(th)}$  vs.  $T_J$**

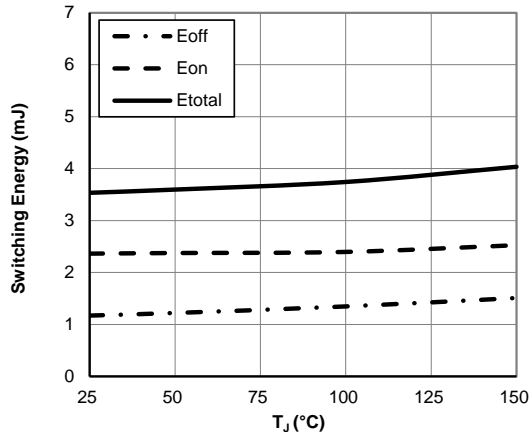


**Figure 17: Switching Loss vs.  $I_C$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $R_g=5\Omega$ )

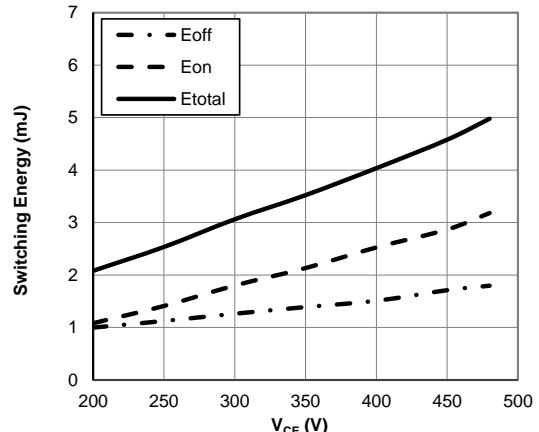


**Figure 18: Switching Loss vs.  $R_g$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $I_C=60\text{A}$ )

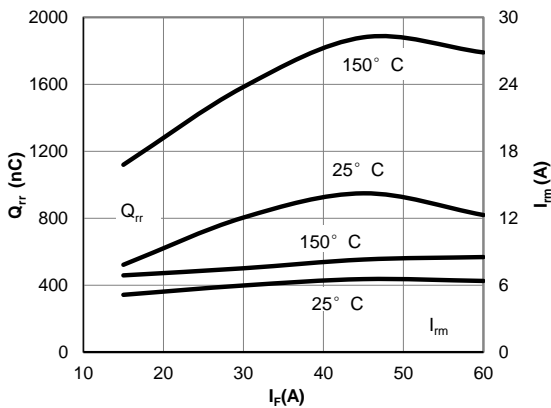
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



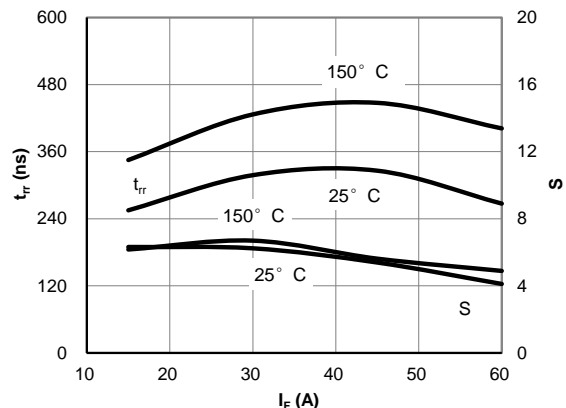
**Figure 19: Switching Loss vs.  $T_j$**   
( $V_{GE}=15V$ ,  $V_{CE}=400V$ ,  $I_C=60A$ ,  $R_g=5\Omega$ )



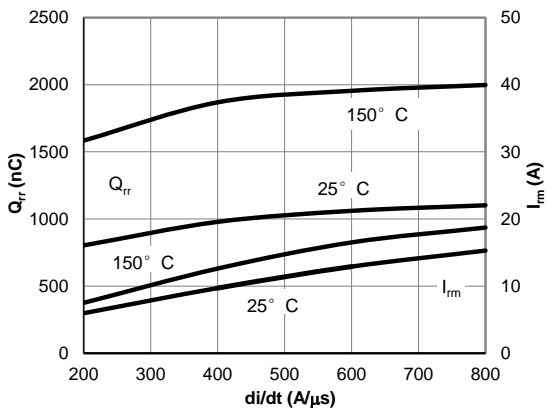
**Figure 20: Switching Loss vs.  $V_{CE}$**   
( $T_j=150^\circ C$ ,  $V_{GE}=15V$ ,  $I_C=60A$ ,  $R_g=5\Omega$ )



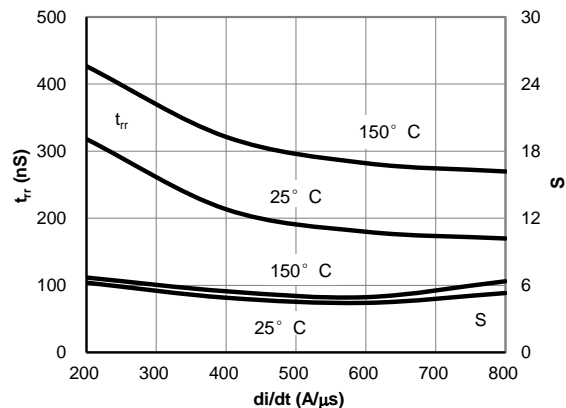
**Figure 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current**  
( $V_{GE}=15V$ ,  $V_{CE}=400V$ ,  $di/dt=200A/\mu s$ )



**Figure 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current**  
( $V_{GE}=15V$ ,  $V_{CE}=400V$ ,  $di/dt=200A/\mu s$ )

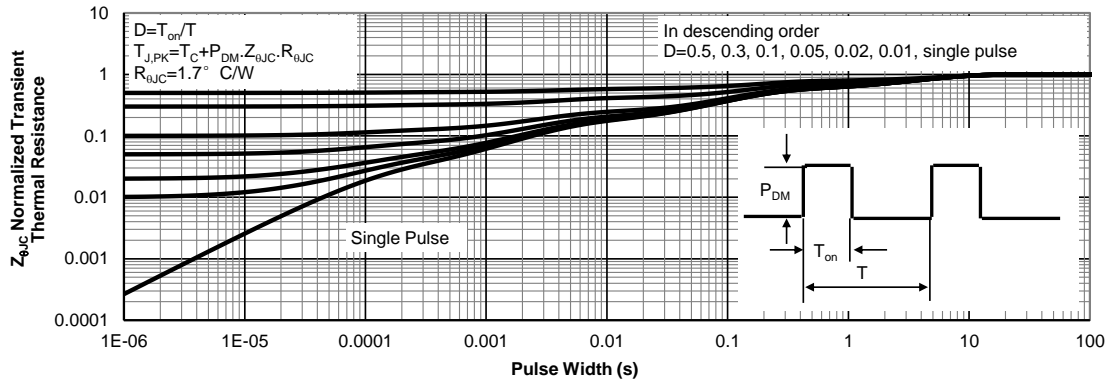


**Figure 23: Diode Reverse Recovery Charge and Peak Current vs.  $di/dt$**   
( $V_{GE}=15V$ ,  $V_{CE}=400V$ ,  $I_F=30A$ )

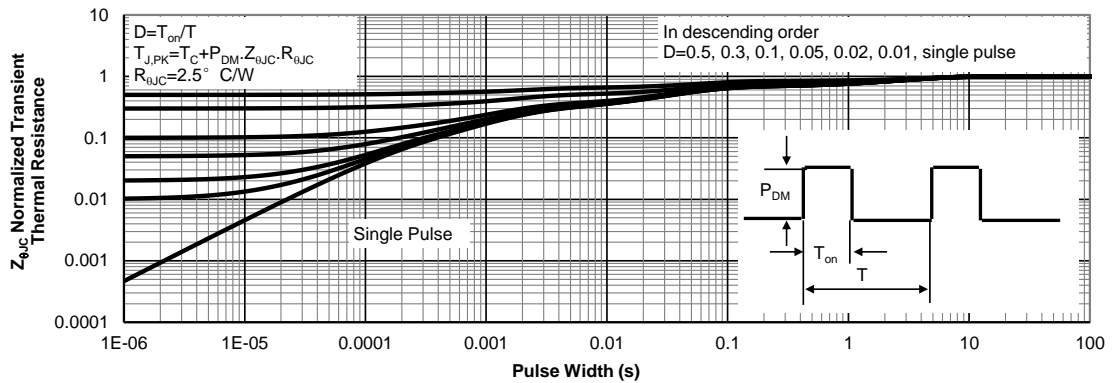


**Figure 24: Diode Reverse Recovery Time and Softness Factor vs.  $di/dt$**   
( $V_{GE}=15V$ ,  $V_{CE}=400V$ ,  $I_F=30A$ )

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



**Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT**



**Figure 26: Normalized Maximum Transient Thermal Impedance for Diode**

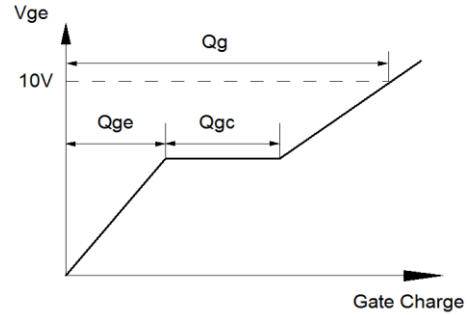
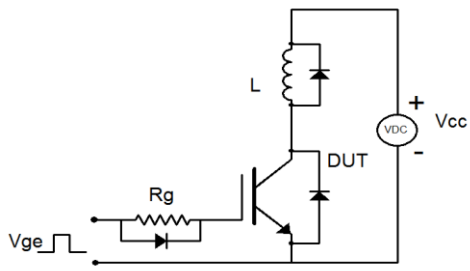


Figure A: Gate Charge Test Circuit & Waveforms

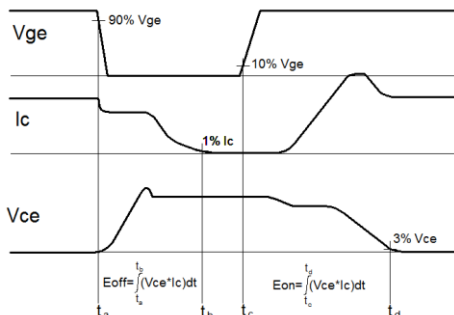
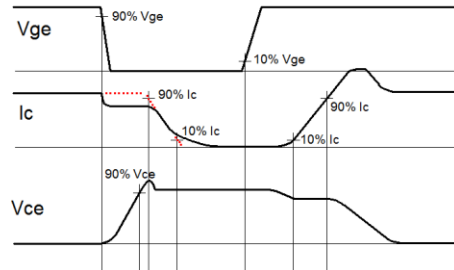
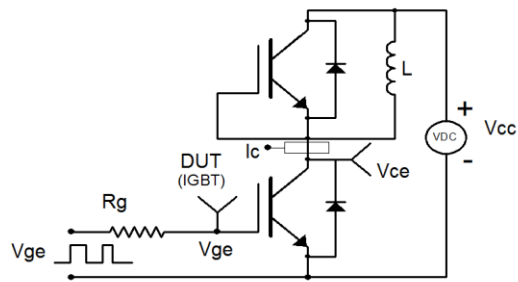


Figure B: Inductive Switching Test Circuit & Waveforms

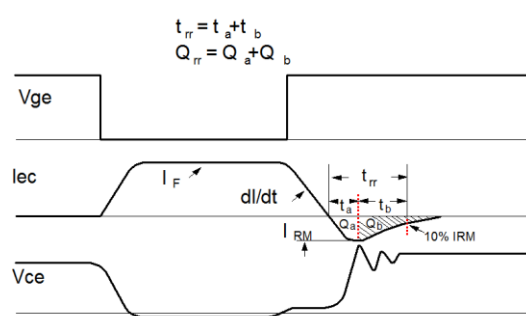
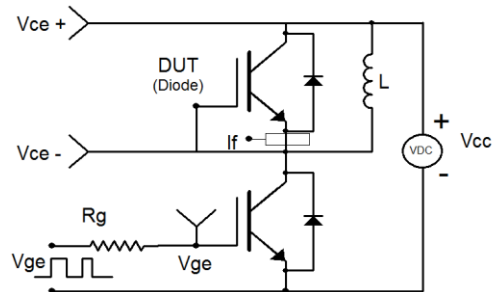


Figure C: Diode Recovery Test Circuit & Waveforms